1.1.2.11 Short Exposure High Power Sensors

1.1.2.11.2 Ariel

200mW to 8000W

Features

- Measures up to 8000W
- Wavelengths: 440 550nm, 900 1100nm, 2.94µm, 10.6µm
- No Water Cooling IP62 rated
- Only 3 seconds to display measurement
- High thermal capacity of 14KJ for uninterrupted consecutive measurements

The Ariel measures high power industrial lasers of up to 8kW by measuring the energy of a short exposure to this power. The laser is set to deliver a pulse of from 0.05 to several seconds. It then measures the energy and duration of the



laser pulse and calculates the power. Ariel can also measure continues power up to 500W intermittently. It is ideal for usage in tight spaces such as additive manufacturing chambers as well as for production process quality control and R&D.

Ariel with window attached

000W e: 0.05 - 2s. ⁶ 0 - 550nm, 90 0 - 550nm, 94 dow or diffuse mx, 2.94μm, 1 nx, >20W; 800 diser: ±30 deg mx: ±25 deg mx: ±25 deg mx: 55% mx: CW; 500V eserating temp	00 - 1100nm (b) 40 - 1100nm (c) er: 2.94µm (c), 10.6µm n diameter for Gaussia leam diameter for Gaus 10.6µm: ±3%; 440 - 55 10 - 1100nm, >10W; >1 100 c) 100	ontinuous depending on position on positio	power level	
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v: 5% r: 25% W: CW; 500V of exposure	W: up to 20s; 1,000W -	·		
of exposure		- 8,000W: 0.05 - 1s.		
of exposure		- 8,000W: 0.05 - 1s.		
perating temp				
perating temp				
	2.4kJ (e) Maximum operating temperature of 60°C will be reached after exposure to 14kJ (e.g. 10 shots at 2.000W.			
0.7s) % Cooling down time before another 14kJ series of shots is ~10 minutes %.				
play				
(f)				
le. 1100mAh.	, lifetime >15 hours			
		atible with Bluetooth 4 a	nd above). USB-C	
mm (see dra				
(- 5/			
IP62 StarLab (PC, USB), StarViewer (iOS or Android, Bluetooth)				
,	Recommended	Min 1/e² beam dia. m	Min 1/e² beam dia. mm diffuser (max dia. is 10mm) mm	
		1	0.3	
		_	2	
			1	
			1	
			1.5	
			3.5	
			N.A.	
			1 807 %	
China RoHS	0.0	22		
	r, USB), Star\	r W Recommended Exposure s Continuous ® 20 ® 2 1 0.7 0.5	Recommended Exposure s Continuous (6) 4 20 (7) 4 2 4 1 6 0.7 10 0.5 16 0.3 22	

Notes: (a) The power is calculated by measuring the pulse energy and exposure time. A rectangular pulse is assumed for this calculation.

(b) May be used at 550 - 900nm with decreased accuracy and higher reflection (up to 10%).

(c) Use without window or diffuser. The sensor does not measure pulse width above 1100nm. For pulsed power measurement at >1100nm, a short pulse with known duration should be applied. A pulse energy measurement is performed and divided by the known pulse width to obtain the power. When working without window and without diffuser, the sensor is not sealed against dust or water.

(d) With diffuser, reading will be up to 10% lower than vertical beam and beam should be offset from center in opposite direction to beam incidence by ~10mm.

(e) At room temperature.

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(f) Faster cooling can be achieved by attaching the Ariel to a heat sink using the mounting threads at the bottom

^{*} For drawings and pictures please see page 106

Ariel









